	Application No.	Applicant(s)
Notice of Allowability	10/767,179	OKITA, YOICHI
Notice of Allowability	Examiner	Art Unit
	Hoai v Pham	2814
The MAILING DATE of this communication appearable claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) of NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGOT (Control of the Office or upon petition by the applicant. See 37 CFR 1.313	OR REMAINS) CLOSED in this apport of the communication GHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. This communication is responsive to 30 January 2004.		
2. 🔀 The allowed claim(s) is/are <u>11-20</u> .		
3. $igotimes$ The drawings filed on <u>30 January 2004</u> are accepted by the	Examiner.	
 4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some* c) None of the: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 10/269,060. 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient. 6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted. (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached 1) hereto or 2) Depen No./Mail Date (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d). 7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL. 		
 Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/0: Paper No./Mail Date 30 January 2004 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material 	6. ☐ Interview Summary Paper No./Mail Da 8), 7. ☑ Examiner's Amendr	te

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DETAILED ACTION

Examiner's amendment

- 1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.
- 2. The application has been amended as follows:

In the specification:

Change the title to: --METHOD OF MANUFACTURING THE FERAM
SEMICONDUCTOR DEVICE WITH IMPROVED CONTACT PLUG STRUCTURE---

In the preliminary amendment dated January 30, 2004, after "application Serial No. 10/269,060 filed October 11, 2002" insert --, now U.S. Pat. No. 6,720,600--.

Allowable Subject Matter

- 3. Claims 11-20 are allowed.
- 4. The following is an examiner's statement of reasons for allowance: the prior of record fails to disclose the combination of the process steps of forming a semiconductor device recited in the base claim, including the combination of the process steps comprising: forming a second insulating layer made of material, that is etched selectively from the capacitor protection layer, over the capacitor protection layer and the first insulating layer; forming a first hole, which comes into contact with the capacitor protection layer on the side surface of the capacitor, in the second insulating layer; and

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forming a first conductive plug, which is connected electrically to the first impurity diffusion region, in the first hole.

- 5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hoai v Pham whose telephone number is 571-272-1715. The examiner can normally be reached on M-F.
- 6. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.
- 7. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hoai Pham

Patent Examiner